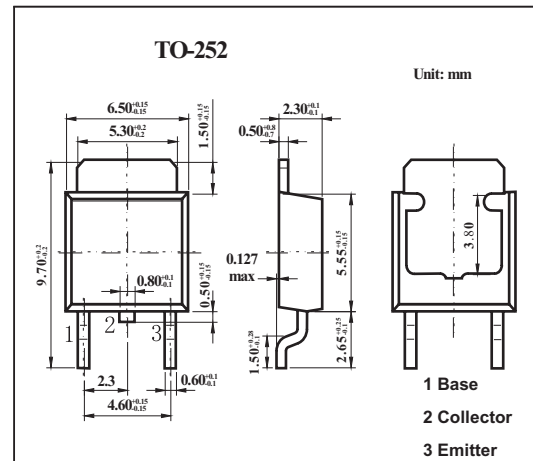


Silicon PNP Epitaxial

2SB906

■ Features

- Low collector saturation voltage.
- High power dissipation.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-7	V
Collector current	I_C	-3	mA
Base current	I_B	-0.5	mA
Collector power dissipation	P_C	1	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{ V}, I_E = 0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7\text{ V}, I_C = 0$			-100	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -50\text{ mA}, I_B = 0$	-60			V
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}$	60		200	
		$V_{CE} = -5\text{ V}, I_C = -3\text{ A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3\text{ A}, I_B = -0.3\text{ A}$		-1	-1.7	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}$		-1	-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		150		pF
Turn-on time	t_{on}	$-I_{B1} = I_{B2} = 0.2\text{ A}, V_{CC} = -30\text{ V}, \text{duty cycle } 1\%$		0.4		μs
Storage time	t_{stg}			1.7		μs
Fall time	t_f			0.5		μs

■ h_{FE} Classification

Rank	O	Y
h_{FE}	60~120	100~200